2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general–purpose amplifier and switching applications.

Features

- High DC Current Gain
- High Current Gain Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|--------------|-----------|
| Collector–Emitter Voltage 2N6487, 2N6490 2N6488, 2N6491 | V _{CEO} | 60 80 | Vdc |
| Collector–Base Voltage 2N6487, 2N6490 2N6488, 2N6491 | V _{CB} | 70 90 | Vdc |
| Emitter-Base Voltage | V _{EB} | 5.0 | Vdc |
| Collector Current – Continuous | Ι _C | 15 | Adc |
| Base Current | Ι _Β | 5.0 | Adc |
| Total Power Dissipation @ T _C = 25°C Derate above 25°C | P _D | 75 0.6 | W W/°C |
| Total Power Dissipation @ T _A = 25°C Derate above 25°C | P _D | 1.8 0.014 | W W/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -65 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data.

THERMAL CHARACTERISTICS

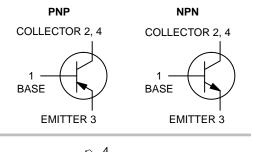
| Characteristics | Symbol | Max | Unit |
|---|----------------|------|------|
| Thermal Resistance, Junction-to-Case | R_{\thetaJC} | 1.67 | °C/W |
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 70 | °C/W |



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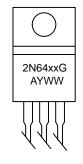
www.onsemi.com

15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60–80 VOLTS, 75 WATTS





MARKING DIAGRAM



2N64xx = Specific Device Code

- xx = See Table on Page 5 G = Pb-Free Package
- G = Pb–Free Package A = Assembly Location
 - Assembly LocationYear
- Y = Year WW = Work Week

ORDERING INFORMATION See detailed ordering, marking, and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Downloaded from Arrow.com.

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

| ELECTRICAL CH | HARACTERISTICS (To | c = 25°C unless othe | erwise noted) (Note 2) |
|---------------|--------------------|----------------------|------------------------|
|---------------|--------------------|----------------------|------------------------|

| Characteristic | Symbol | Min | Мах | Unit |
|--|-----------------------|-------------|--------------------------|------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 200 \text{ mAdc}, I_B = 0$) 2N6487, 2N6490 2N6488, 2N6491 | V _{CEO(sus)} | 60 80 | | Vdc |
| Collector–Emitter Sustaining Voltage (Note 3) (I _C = 200 mAdc, V _{BE} = 1.5 Vdc) 2N6487, 2N6490 2N6488, 2N6491 | V _{CEX} | 70 90 | | Vdc |
| Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0) 2N6487, 2N6490 (V _{CE} = 40 Vdc, I _B = 0) 2N6488, 2N6491 | ICEO | - | 1.0 1.0 | mAdc |
| Collector Cutoff Current ($V_{CE} = 65 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) 2N6487, 2N6490 ($V_{CE} = 85 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) 2N6488, 2N6491 ($V_{CE} = 60 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}$) 2N6487, 2N6490 ($V_{CE} = 80 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}$) 2N6488, 2N6491 | ICEX | - - - | 500 500 5.0 5.0 | μAdc |
| Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$) | I _{EBO} | _ | 1.0 | mAdc |
| ON CHARACTERISTICS | | | | |
| DC Current Gain ($I_C = 5.0$ Adc, $V_{CE} = 4.0$ Vdc) ($I_C = 15$ Adc, $V_{CE} = 4.0$ Vdc) | h _{FE} | 20 5.0 | 150 - | - |
| Collector–Emitter Saturation Voltage ($I_C = 5.0 \text{ Adc}, I_B = 0.5 \text{ Adc}$) ($I_C = 15 \text{ Adc}, I_B = 5.0 \text{ Adc}$) | V _{CE(sat)} | | 1.3 3.5 | Vdc |
| Base-Emitter On Voltage ($I_C = 5.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) ($I_C = 15 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) | V _{BE(on)} | | 1.3 3.5 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | |
| Current–Gain – Bandwidth Product (Note 4) ($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$) | f _T | 5.0 | _ | MHz |
| | | | 1 | 1 |

Small–Signal Current Gain
($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 1.0 \text{ kHz}$)h----

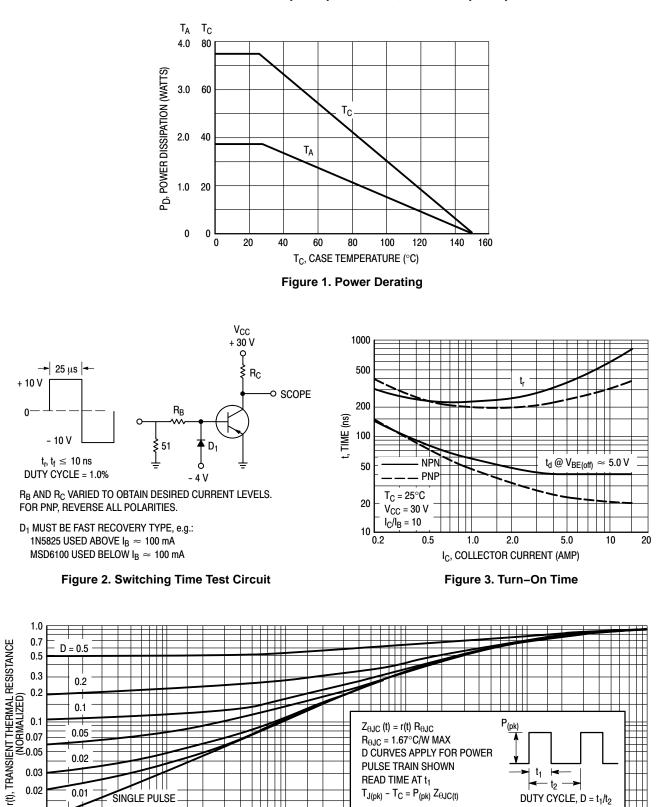
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Indicates JEDEC Registered Data.

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

4. $f_T = |h_{fe}| \bullet f_{test}$

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)





2.0

1.0

 $T_{J(pk)} - T_C = P_{(pk)} Z_{\Theta JC(t)}$

10

20

5.0

t, TIME (ms) **Figure 4. Thermal Response** t₂

100

50

DUTY CYCLE, $D = t_1/t_2$

200

500 1.0 k

0.01

0.02

0.01 🛏 0.01

SINGLE PULSE

0.05

0.1

0.2

0.5

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

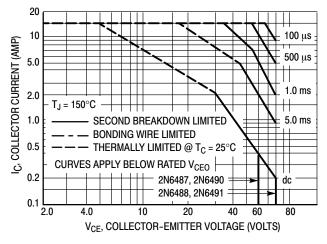


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistors average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

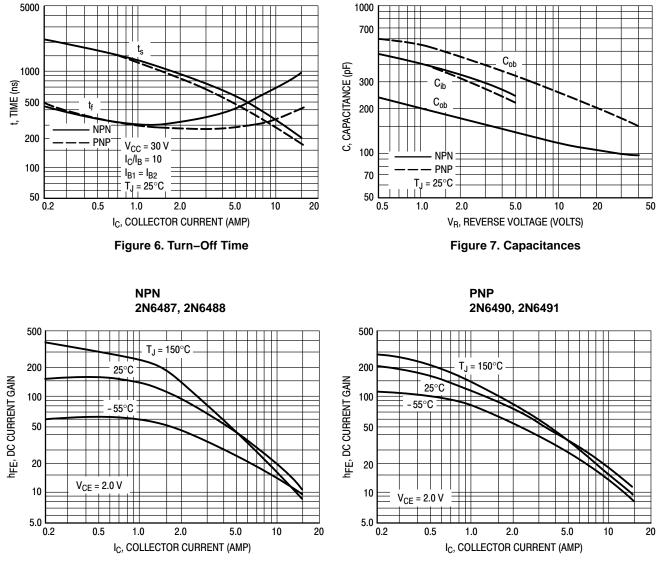


Figure 8. DC Current Gain

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

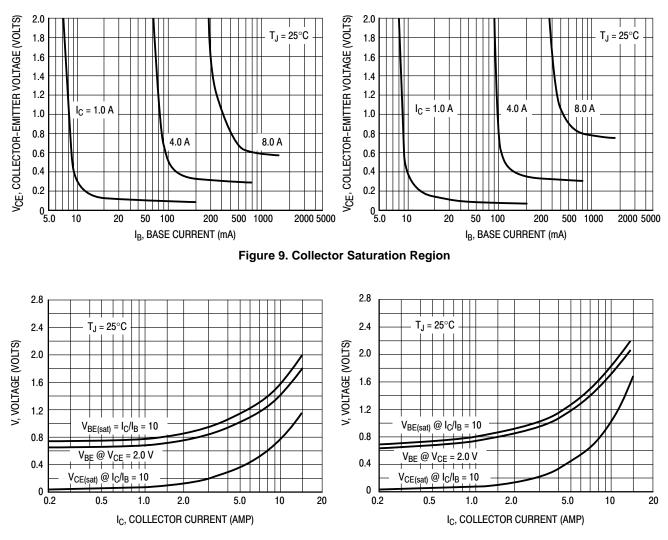


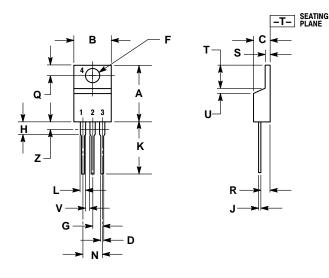
Figure 10. "On" Voltages

ORDERING INFORMATION

| Device | Device Marking | Package | Shipping |
|---------|----------------|---------------------|-----------------|
| 2N6487G | 2N6487 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6488G | 2N6488 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6490G | 2N6490 | TO-220 (Pb-Free) | 50 Units / Rail |
| 2N6491G | 2N6491 | TO-220 (Pb-Free) | 50 Units / Rail |

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AH**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED

| | INCHES | | MILLIN | ETERS |
|-----|--------|-------|--------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.415 | 9.66 | 10.53 |
| С | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| κ | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| Ν | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| Т | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ۷ | 0.045 | | 1.15 | |
| Ζ | | 0.080 | | 2.04 |

STYLE 1: BASE PIN 1. 2. COLLECTOR FMITTER 3 COLLECTOR

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